

Source/Drain Diffusion Resistor

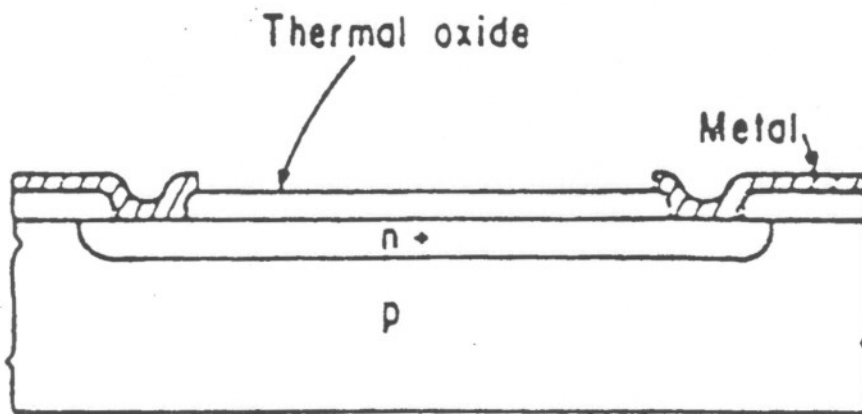


Fig: Resistor formed in source-drain diffusion.

$$R_{\square} = 20 - 80 \Omega/\square$$

$$\text{TCR} = 500 - 1500 \text{ppm}/^{\circ}\text{C}$$

$$\text{Tolerance} = \pm 15\%$$

Polysilicon Resistor

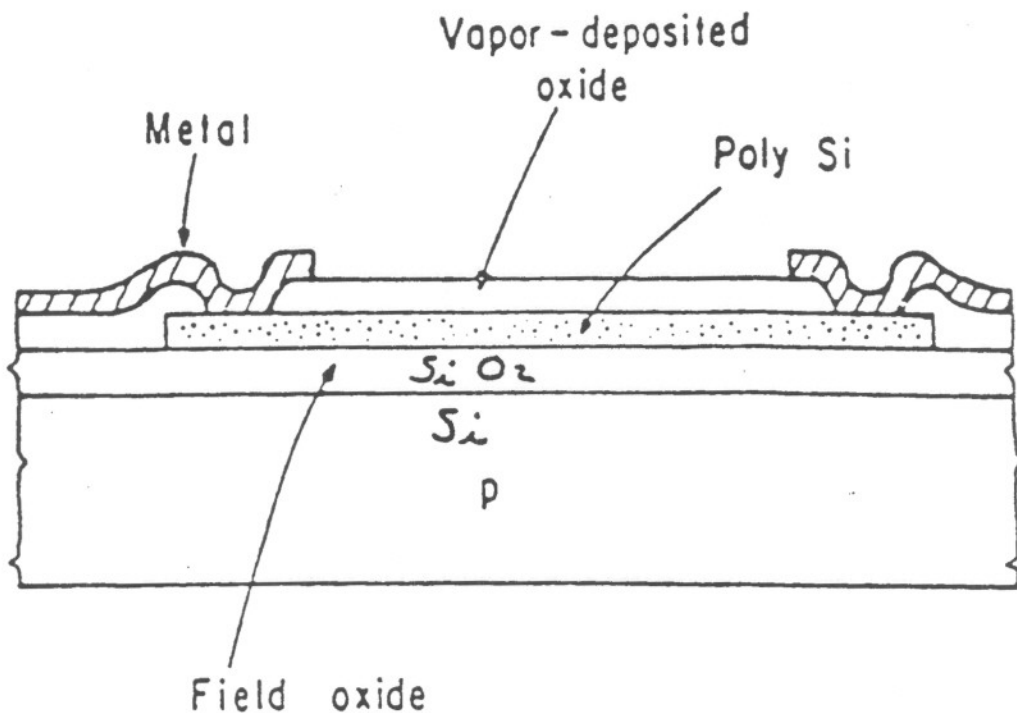


Fig: Resistor formed in polysilicon.

$$R_{\square} \approx 20 - 80 \Omega/\square$$

$$\text{TCR} \approx 500 - 1500 \text{ppm}/^{\circ}\text{C}$$

$$\text{Tolerance} = \pm 10\%$$

Usually denser than diffused resistor.

Well Resistor (CMOS)

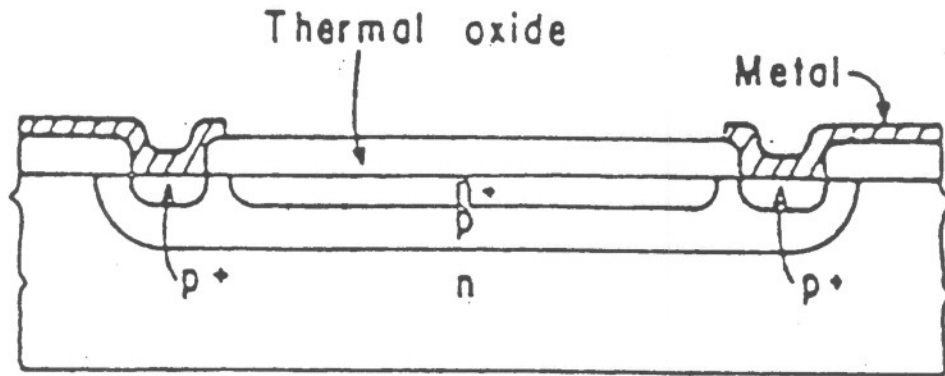


Fig: "Pinched" resistor in a CMOS well.

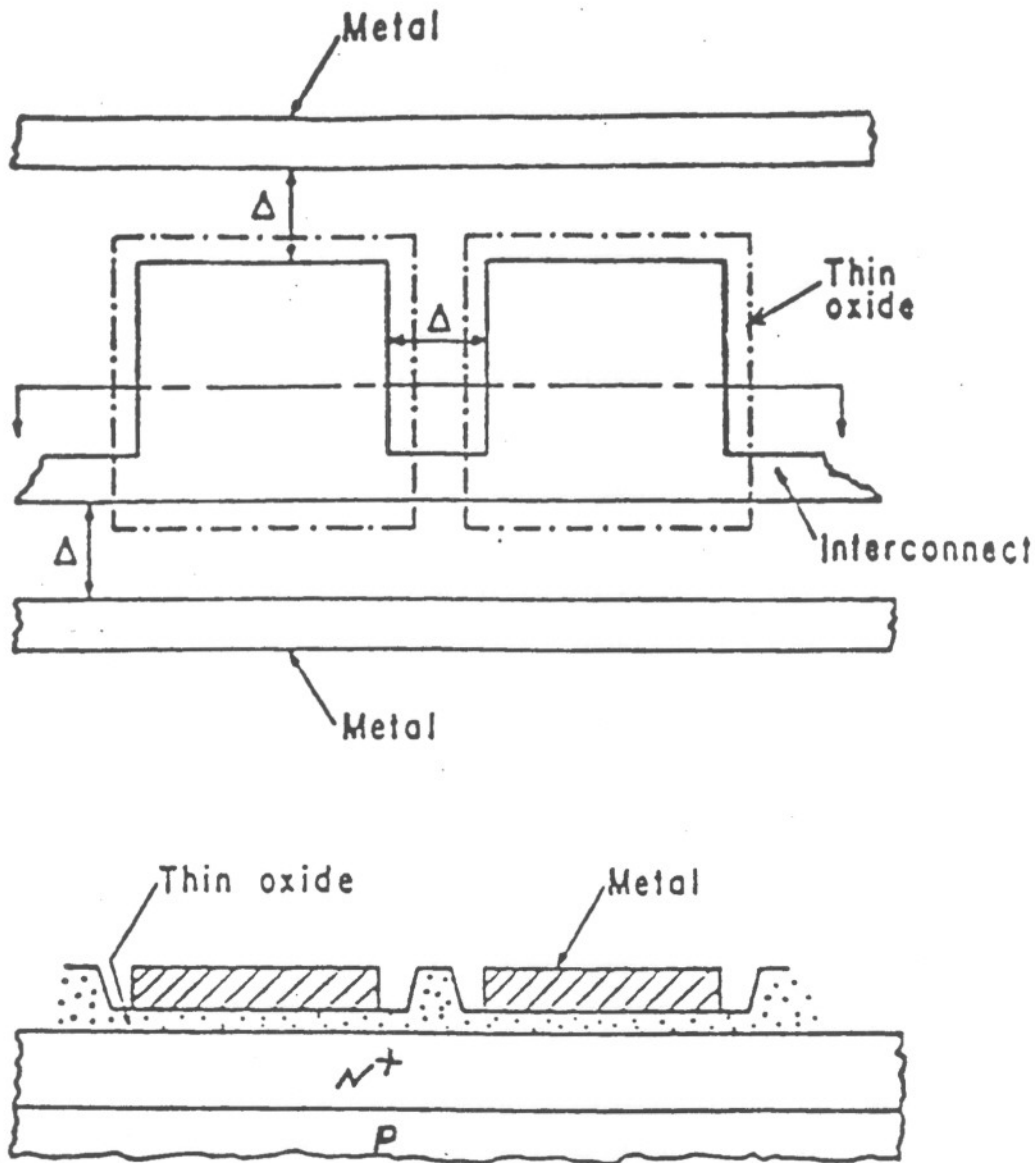
$$R_{\square} \approx 1k - 5k\Omega/\square$$

$$TCR \approx 4000\text{ppm}/^{\circ}\text{C}$$

$$\text{Tolerance} \approx \pm 20\%$$

Large VCR

Capacitors: Metal-Diffusion



C	=	$3.7\text{fF}/\mu^2$	@	100	Å
TCC	≈	$25\text{ppm}/^\circ\text{C}$			
Tolerance	≈	$\pm 10\%$			
VCC	≈	$25\text{ppm}/\text{V}$			

Poly to Silicon

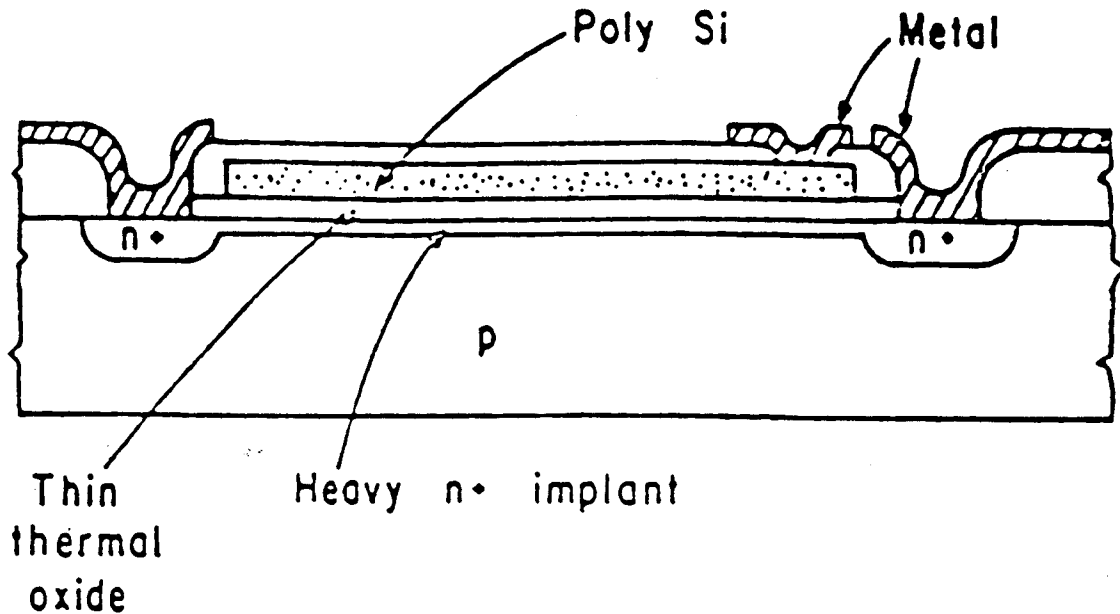


Fig: Capacitor with polysilicon as top plate and heavily implanted bottom plate.

Requires extra mask

Useful for single poly

Properties like metal-diffusion if bottom plate is heavily doped

Poly-Poly Capacitor

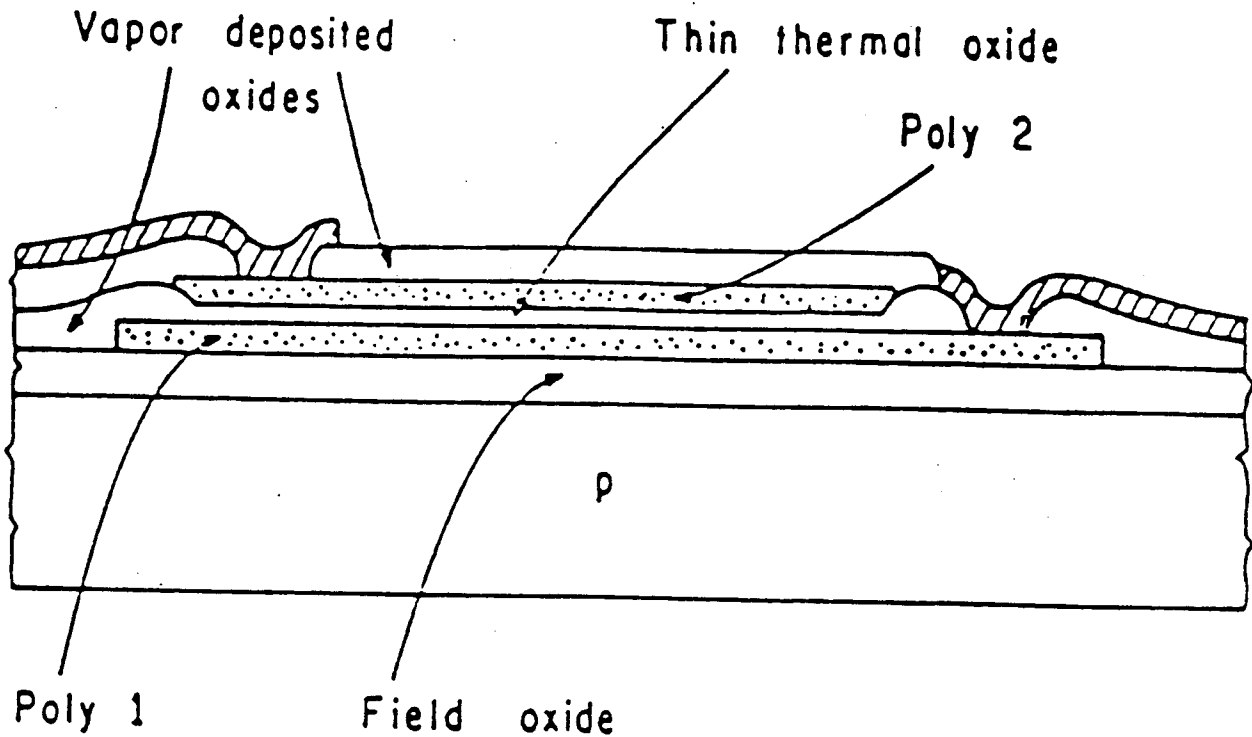


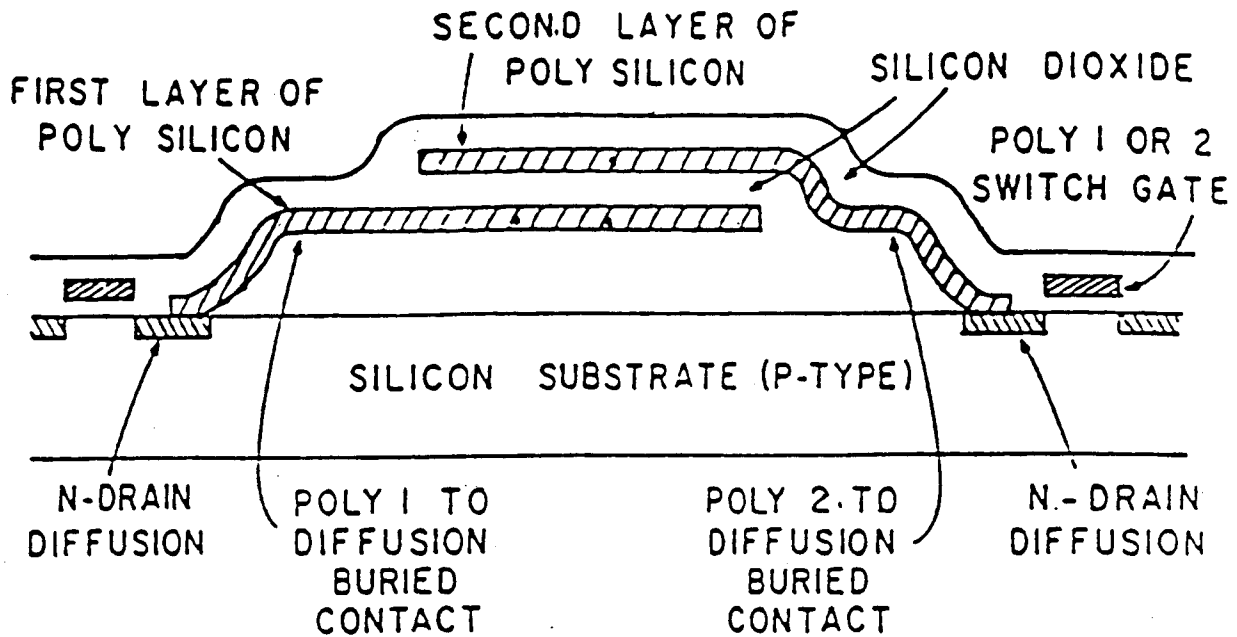
Fig: Capacitor uses two layers of poly-silicon. The dielectric oxide is formed by thermally oxidizing poly 1 before depositing poly 2.

Requires double-poly

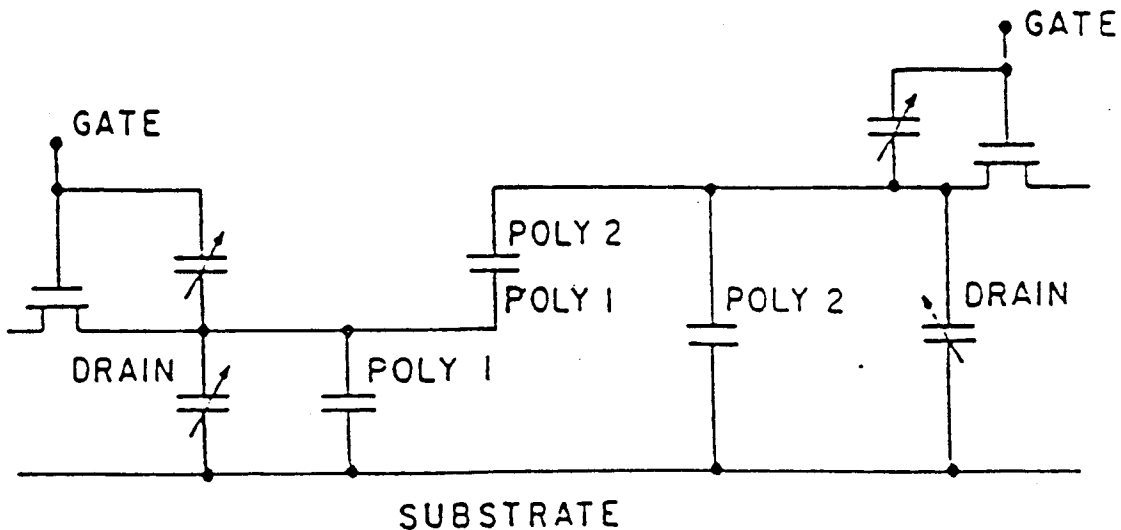
TCC \approx 100ppm/ $^{\circ}$ C

VCC \approx 100ppm/V

Polysilicon Capacitor and Switch Structure



CIRCUIT MODEL



Component Matching Data

Component	Fabrication technique	Matching	Temperature coefficient	Voltage coefficient
Resistors	Diffused	$\pm 0.4\%$	$+2000\text{ppm}/^\circ\text{C}$	$\sim 200\text{ppm}/\text{V}$
	Ion-implanted	$\pm 0.12\%$	$+400\text{ppm}/^\circ\text{C}$	$\sim 800\text{ppm}/\text{V}$
Capacitors	MOS $t_{\text{ox}} = 0.1\mu$	$\pm 0.06\%$	$26\text{ppm}/^\circ\text{C}$	$10\text{ppm}/\text{V}$

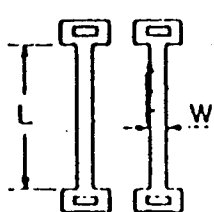
Component Matching Considerations

a) Lithographic Resolution Limit

Resistors $R = R_s \frac{L}{W}$ $R_s: \Omega/\square$ \equiv

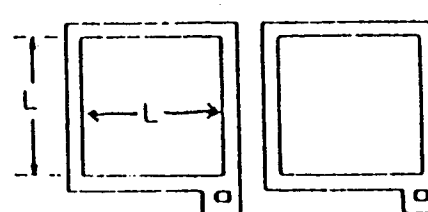
$$\frac{\Delta R}{R} = \frac{\Delta L}{L} - \frac{\Delta W}{W}$$

$$\frac{\Delta R}{R} \approx \frac{\Delta W}{W}$$



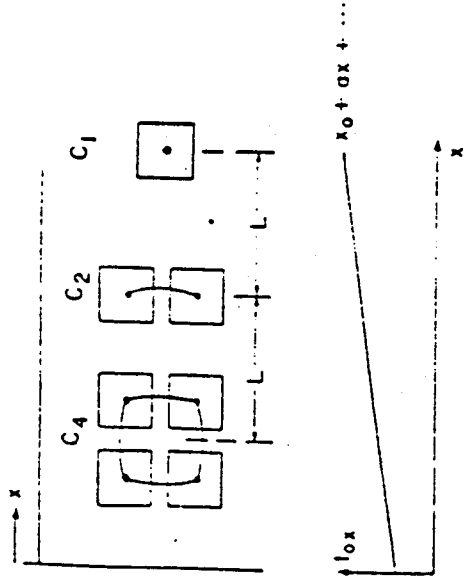
Capacitors $C = C_{\text{ox}} L^2$ $C_{\text{ox}}: \text{pF}/\text{mil}^2$

$$\frac{\Delta C}{C} = 2 \frac{\Delta L}{L}$$

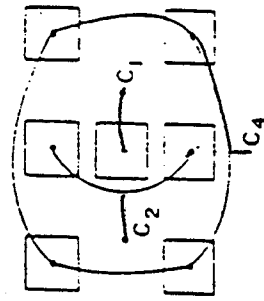


Key point: Use large geometries

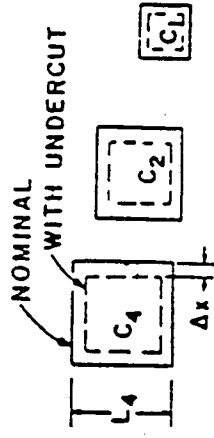
Gradient Insensitive Structures



Common Centroid Geometry



Undercut Insensitive Structures



Undercut - Insensitive Geometry

